March 2000



FDP5645/FDB5645 60V N-Channel PowerTrench® MOSFET

General Description

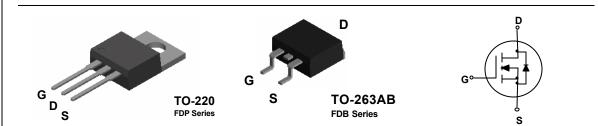
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $R_{DS(ON)}$ specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

Features

- 80 A, 60 V. $R_{_{DS(ON)}} = 0.0095 \ \Omega \ @ V_{_{GS}} = 10 \ V$ $R_{DS(ON)} = 0.011 \ \Omega @ V_{GS} = 6 \ V.$
- · Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- High performance trench technology for extremely low R_{DS(ON)}.
- 175°C maximum junction temperature rating.



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter	FDP5645 FDB5645	Units
V _{DSS}	Drain-Source Voltage	60	V
V _{GSS}	Gate-Source Voltage	±20	V
D	Maximum Drain Current – Continuous (note 3)	80	A
	– Pulsed	300	
PD	Total Power Dissipation $@T_c = 25^{\circ}C$	125	W
	Derate above 25°C	0.83	W/°C
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-65 to +175	°C
TL	Maximum lead termperature for soldering purposes, 1/8" from case for 5 seconds	+275	°C
Therma	I Characteristics		
R _{eJC}	Thermal Resistance, Junction-to-Case	1.2	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	°C/W

Thermal Resistance, Junction-to-Ambient $R_{\theta JA}$

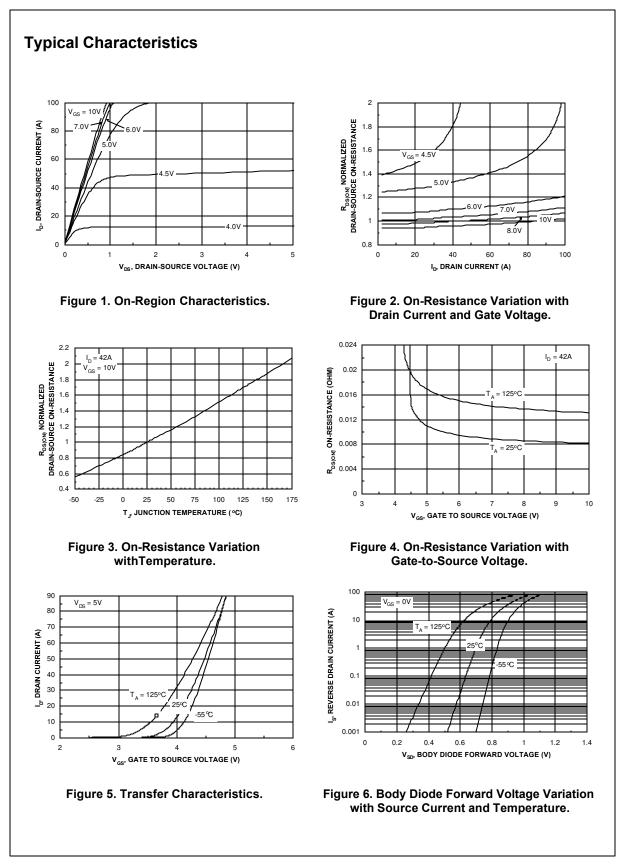
Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDB5645	FDB5645	13"	24mm	800 units
FDP5645	FDP5645	note 2		

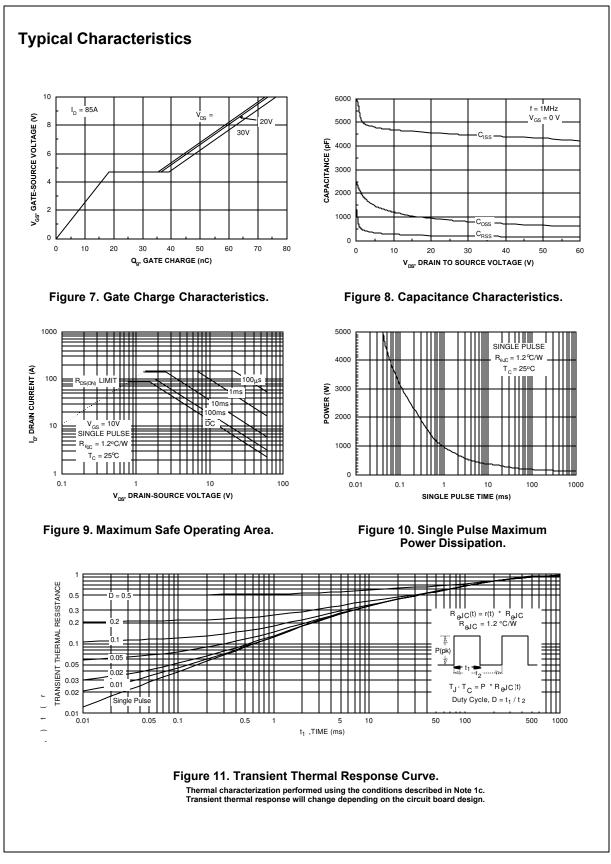
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Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Drain-Sc	burce Avalanche Ratings (Note 1)				
W _{DSS}	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 40 \text{ V}, I_D = 80 \text{ A}$			800	mJ
AR	Maximum Drain-Source Avalanche Current				80	A
Off Char	racteristics					
BV _{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0 V, I_D = 250 \mu A$	60			V
<u>ΔBV dss</u> ΔTj	Breakdown Voltage Temperature Coefficient	$l_{\rm D}$ = 250 µA, Referenced to 25°C		64		mV/ºC
DSS	Zero Gate Voltage Drain Current	$V_{DS} = 48 \text{ V}, \qquad V_{GS} = 0 \text{ V}$			1	μA
GSSF	Gate-Body Leakage, Forward	$V_{GS} = 20 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
GSSR	Gate-Body Leakage, Reverse	$V_{GS} = 20 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			-100	nA
	acteristics (Note 1)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2	1	4	V
<u>ΔVgs(th)</u> ΔTj	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}$, Referenced to 25°C		-7.8		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$ \begin{array}{c c} V_{\rm GS} = 10 \ V, & l_{\rm D} = 40 \ A \\ V_{\rm GS} = 10 V, & l_{\rm D} = 40 \ A, \ T_{\rm J} = 125^\circ C \\ V_{\rm GS} = 6 \ V, & l_{\rm D} = 38 \ A \end{array} $		8 13 9	9.5 18 11	mΩ
D(on)	On-State Drain Current	$V_{GS} = 10 \text{ V}, \qquad V_{DS} = 10 \text{ V}$	60			Α
g fs	Forward Transconductance	$V_{DS} = 5 V$, $I_D = 40 A$		88		S
Dvnamio	Characteristics	•				
C _{iss}	Input Capacitance	$V_{DS} = 30 V$, $V_{GS} = 0 V$,		4468		pF
Coss	Output Capacitance	f = 1.0 MHz		810		pF
C _{rss}	Reverse Transfer Capacitance			198		pF
	Turn–On Delay Time	$V_{DD} = 30 V$, $I_D = 1 A$,		21	30	ns
d(on)	Turn-On Rise Time	$V_{DD} = 30 V$, $I_D = 1 A$, $V_{GS} = 10 V$, $R_{GEN} = 6 \Omega$		13	20	-
		$V_{\rm GS} = 10$ V, $\Gamma_{\rm GEN} = 0.22$		77	20 90	ns
d(off)	Turn–Off Delay Time	-		42	90 50	ns
f						ns
	Total Gate Charge	$V_{DS} = 30 \text{ V}, \qquad I_D = 80 \text{ A}, \\ V_{GS} = 10 \text{ V}$		76	107	nC
	Gate-Source Charge	-		18		nC
Q _{gd}	Gate-Drain Charge			21		nC
Drain-S	ource Diode Characteristics a					-
S	Maximum Continuous Drain-Source			 	80	A
s V _{SD}	Maximum Pulsed Drain–Source Diod Drain–Source Diode Forward Voltage	$V_{GS} = 0 V, I_S = 40 A$		0.9	300 1.3	A V
tes:		•	L	I	1	ı
	llse Width < 300μs, Duty Cycle < 2.0%					

FDP5645/FDB5645

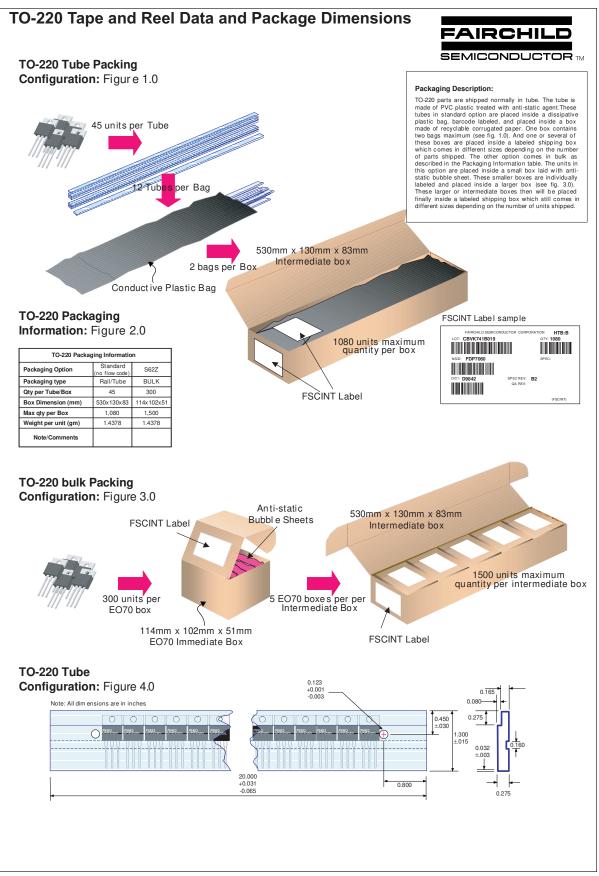


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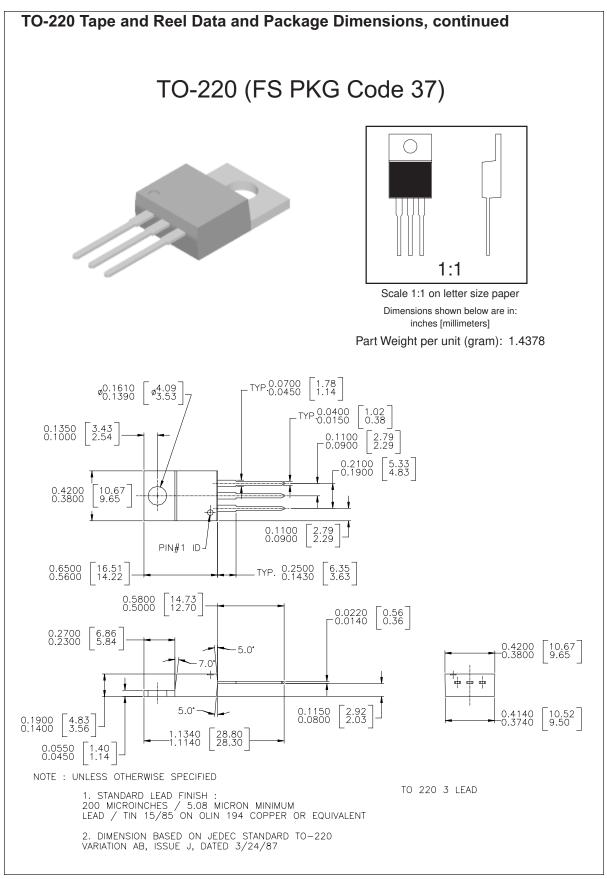


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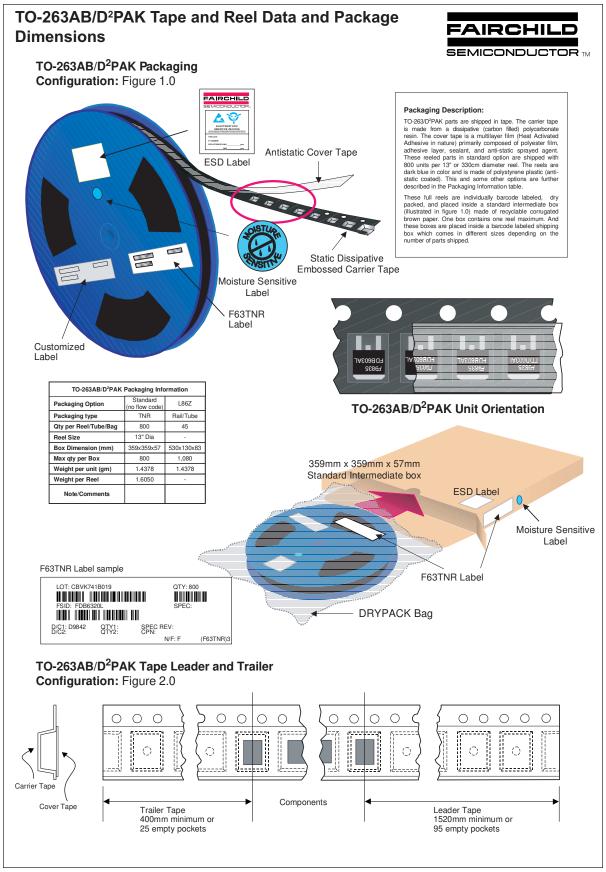
FDP5645/FDB5645 Rev. B (W)



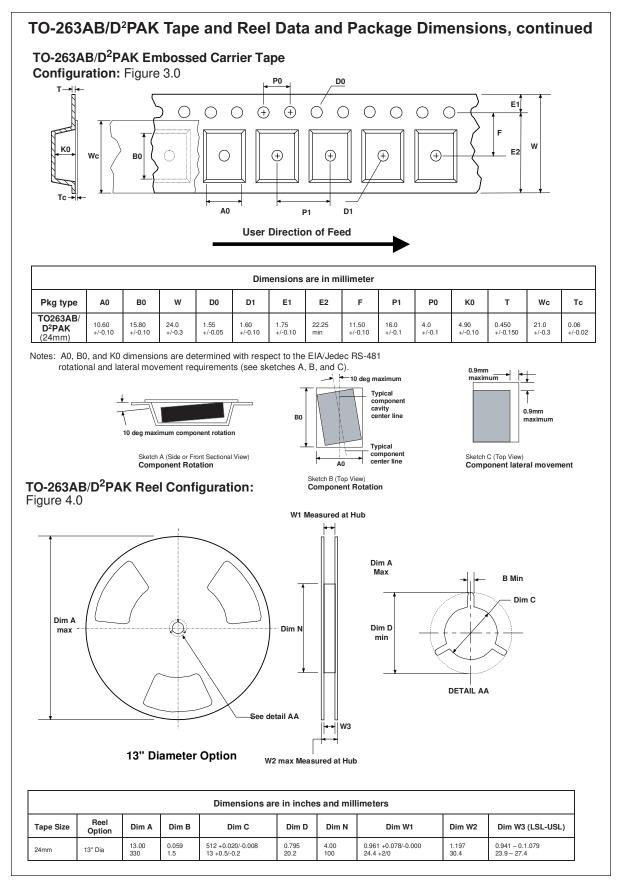
August 1999, Rev. B

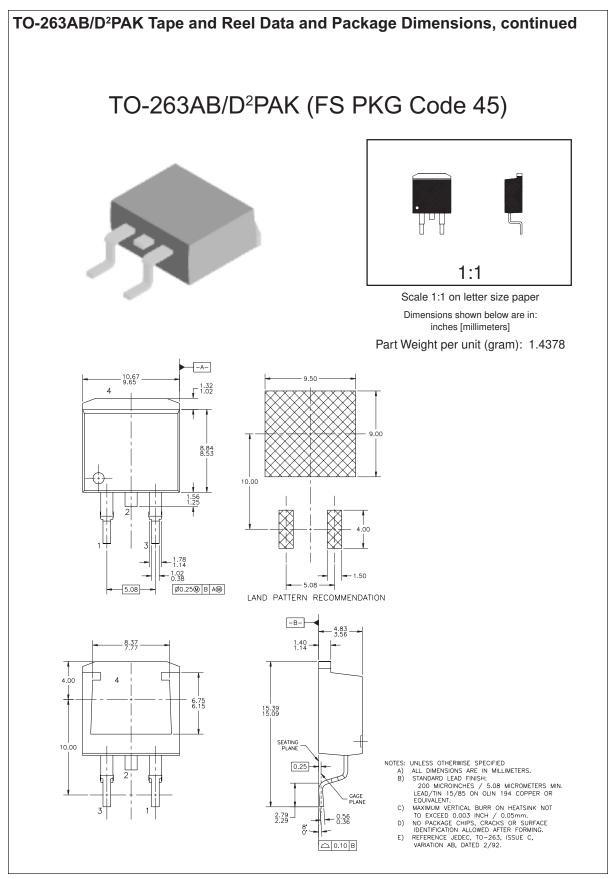


September 1998, Rev. A



September 1999, Rev. B





August 1998, Rev. A

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